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Hex Inverter

The MC74VHCT04A is an advanced high speed CMOS inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5 V CMOS level output swings.

The VHCT04A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC}=0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 4.7 \text{ ns (Typ)}$ at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.0 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 48 FETs or 12 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week

G or ■ = Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| | Device | Package | Shipping [†] |
|--------|-------------|----------------------|-----------------------|
| MC74V | HCT04ADR2G | SOIC-14 (Pb-Free) | 2500 / Tape & Reel |
| MC74VI | HCT04ADTR2G | TSSOP14 (Pb-Free) | 2500 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

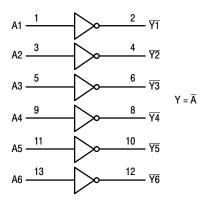


Figure 1. Logic Diagram

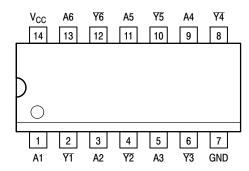


Figure 2. Pinout: 14-Lead Packages (Top View)

FUNCTION TABLE

| Inputs | Outputs |
|--------|---------|
| Α | Y |
| L | Н |
| Н | L |

MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit |
|------------------|--|-------------------|--|------|
| V _{CC} | DC Supply Voltage | | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage | | - 0.5 to + 7.0 | V |
| V _{out} | DC Output Voltage V High or Lov | CC = 0 v State | - 0.5 to + 7.0 - 0.5 to V _{CC} + 0.5 | V |
| I _{IK} | Input Diode Current | | - 20 | mA |
| I _{OK} | Output Diode Current (V _{OUT} < GND; V _{OUT} > V | 'cc) | ± 20 | mA |
| l _{out} | DC Output Current, per Pin | | ± 25 | mA |
| Icc | DC Supply Current, V _{CC} and GND Pins | | ± 50 | mA |
| P _D | Power Dissipation in Still Air, SOIC Pack TSSOP Pack | • | 500 450 | mW |
| T _{stg} | Storage Temperature | | - 65 to + 150 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|---------------------------------|--|------|------------------------|------|
| V _{CC} | DC Supply Voltage | 4.5 | 5.5 | V |
| V _{in} | DC Input Voltage | 0 | 5.5 | V |
| V _{out} | DC Output Voltage $V_{CC} = 0$ High or Low State | 0 | 5.5 V _{CC} | V |
| T _A | Operating Temperature | - 40 | + 85 | °C |
| t _r , t _f | Input Rise and Fall Time V _{CC} =5.0V ±0.5V | 0 | 20 | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

| | | | V _{CC} | | T _A = 25°C | ; | T _A = - 40 to 85°C | | |
|---|--|--|-----------------|-----|-----------------------|-------|-------------------------------|-------|------|
| Symbol | Parameter | Test Conditions | V | Min | Тур | Max | Min | Max | Unit |
| V _{IH} | Minimum High-Level Input Voltage | | 4.5 to 5.5 | 2.0 | | | 2.0 | | V |
| V_{IL} | Maximum Low-Level Input Voltage | | 4.5 to 5.5 | | | 0.8 | | 0.8 | V |
| V_{OH} | Minimum High-Level | $I_{OH} = -50\mu A$ | 4.5 | 4.4 | 4.5 | | 4.4 | | V |
| Output Voltage V _{in} = V _{IH} or V _{IL} | I _{OH} = - 8mA | 4.5 | 3.94 | | | 3.80 | | | |
| V_{OL} | Maximum Low-Level | I _{OL} = 50μA | 4.5 | | 0.0 | 0.1 | | 0.1 | V |
| | Output Voltage V _{in} = V _{IH} or V _{IL} | I _{OL} = 8mA | 4.5 | | | 0.36 | | 0.44 | |
| I _{in} | Maximum Input Leakage Current | V _{in} = 5.5 V or GND | 0 to 5.5 | | | ± 0.1 | | ± 1.0 | μА |
| I _{CC} | Maximum Quiescent Supply Current | V _{in} = V _{CC} or GND | 5.5 | | | 2.0 | | 20.0 | μА |
| I _{CCT} | Quiescent Supply Current | Per Input: V _{IN} = 3.4V Other Input: V _{CC} or GND | 5.5 | | | 1.35 | | 1.50 | mA |
| I _{OPD} | Output Leakage Current | V _{OUT} = 5.5V | 0 | | | 0.5 | | 5.0 | μА |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$)

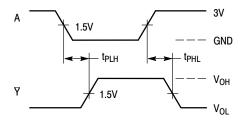
| | | T _A | | T _A = 25°C | | T _A = - 40 to 85°C | | | |
|--|--------------------------------------|--------------------------|------------------------------|-----------------------|------------|-------------------------------|------------|------------|------|
| Symbol | Parameter | Test Condi | tions | Min | Тур | Max | Min | Max | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, A to Y | $V_{CC} = 5.0 \pm 0.5 V$ | $C_L = 15pF$ $C_L = 50pF$ | | 4.7 5.5 | 6.7 7.7 | 1.0 1.0 | 7.5 8.5 | ns |
| C _{in} | Maximum Input Capacitance | | | | 4 | 10 | | 10 | pF |

| | | Typical @ 25°C, V _{CC} = 5.0V | |
|----------|--|--|----|
| C_{PD} | Power Dissipation Capacitance (Note 1) | 11 | pF |

^{1.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/6$ (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$, $C_L = 50 \text{pF}$, $V_{CC} = 5.0 \text{V}$)

| | | T _A = 25°C | | |
|------------------|--|-----------------------|------|------|
| Symbol | Characteristic | Тур | Max | Unit |
| V _{OLP} | Quiet Output Maximum Dynamic V _{OL} | 0.8 | 1.0 | V |
| V _{OLV} | Quiet Output Minimum Dynamic V _{OL} | -0.8 | -1.0 | V |
| V _{IHD} | Minimum High Level Dynamic Input Voltage | | 2.0 | V |
| V _{ILD} | Maximum Low Level Dynamic Input Voltage | | 0.8 | V |



DEVICE UNDER TEST CL*

TEST POINT

*Includes all probe and jig capacitance

Figure 3. Switching Waveforms

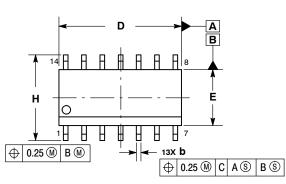
Figure 4. Test Circuit

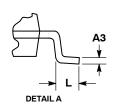


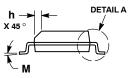
△ 0.10

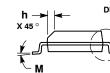
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





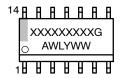




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

| | MILLIN | IETERS | INCHES | |
|-----|--------|--------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 1.35 | 1.75 | 0.054 | 0.068 |
| A1 | 0.10 | 0.25 | 0.004 | 0.010 |
| АЗ | 0.19 | 0.25 | 0.008 | 0.010 |
| b | 0.35 | 0.49 | 0.014 | 0.019 |
| D | 8.55 | 8.75 | 0.337 | 0.344 |
| Е | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 | BSC | 0.050 BSC | |
| Н | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.019 |
| L | 0.40 | 1.25 | 0.016 | 0.049 |
| М | 0 ° | 7° | 0 ° | 7° |

GENERIC MARKING DIAGRAM*



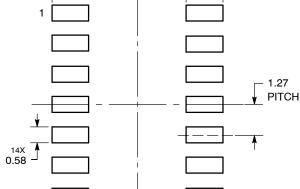
XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

- 6.50 -14X 1.18

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

C SEATING PLANE

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

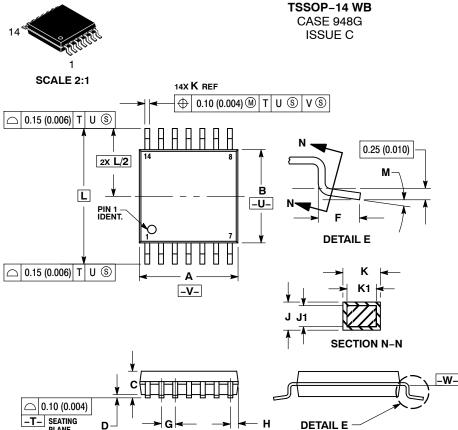
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

| STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 2: CANCELLED | STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE | STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE |
|---|---|---|---|
| STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE | STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE | STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE |

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DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

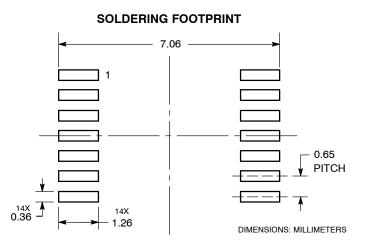
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

| | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.90 | 5.10 | 0.193 | 0.200 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 BSC | | 0.026 BSC | |
| Н | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 BSC | | 0.252 BSC | |
| М | o° | 8 ° | 0 ° | 8 ° |

GENERIC MARKING DIAGRAM*





= Assembly Location

= Wafer Lot = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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